

# Strain distribution in GaN/AlN multi quantum wells studied by X-ray diffraction and photoluminescence

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## Aim of the work:

- to apply X-ray diffraction (XRD) technique to study strain distribution in GaN/AlN multi-quantum-wells (MQWs) grown by plasma-assisted MBE on AlN/sapphire substrates
- to investigate an influence of well/barrier thickness on strain state in MQWs

## Samples studied:

- GaN/AlN MQWs with GaN well and AlN barrier thicknesses from 2 nm to 4 nm
- structures grown on sapphire substrates with AlN layers by plasma assisted molecular beam epitaxy

## Experimental techniques

- X-ray diffraction:
  - 2 $\theta$ / $\omega$  scan of 00.2 AlN/GaN symmetrical reflection
  - reciprocal space map (RSM) of 11.4 AlN/GaN asymmetrical reflection
- Analysis of XRD results:
  - simulation of 00.2 symmetrical 2 $\theta$ / $\omega$  scan by utilizing dynamical theory of X-ray diffraction
  - calculation of lattice constants and strain relation from RSMs
- Transmission electron microscopy (TEM):
  - to check the quality of MQWs interfaces and thicknesses of well/barrier
- Photoluminescence (PL):
  - to compare spectrum coming from MQWs in dependence of well/barrier thickness

## Structure of the samples

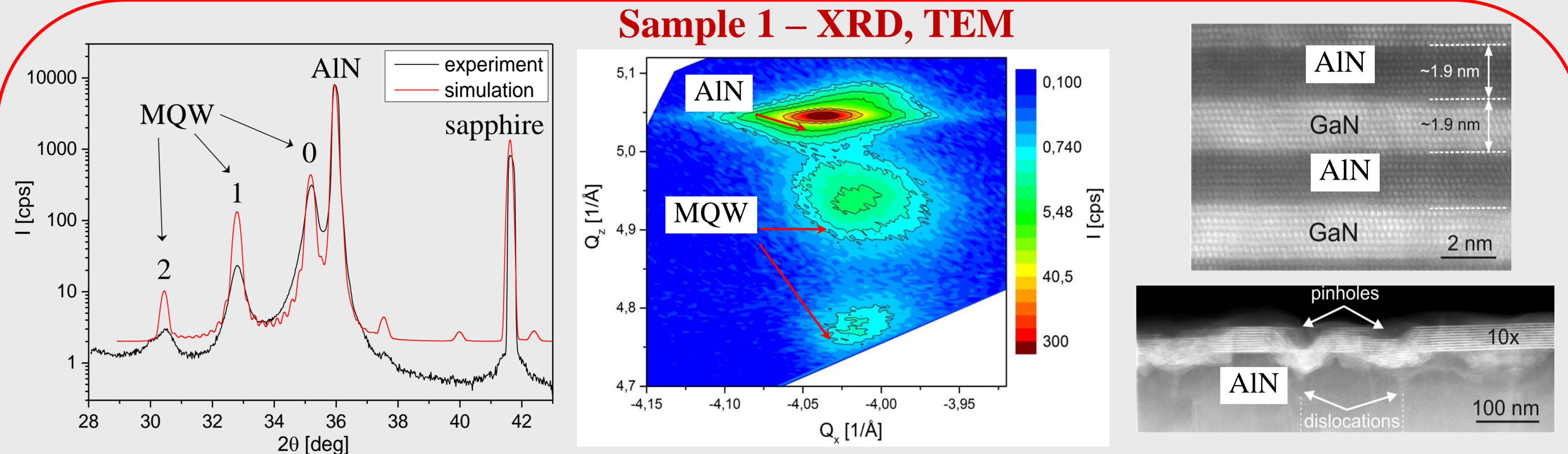
AIN:Si 50 nm	AIN:Si 50 nm	AIN:Si 50 nm
AIN 2 nm GaN 2 nm × 10	AIN 3 nm GaN 3 nm × 10	AIN 4 nm GaN 4 nm × 10
AIN:Si 50 nm	AIN:Si 50 nm	AIN:Si 500 nm
AIN 1 $\mu$ m	AIN 1 $\mu$ m	AIN 3 $\mu$ m
AIN 60 nm	AIN 60 nm	
sapphire	sapphire	sapphire

Sample 1      Sample 2      Sample 3

Theoretical values of lattice constants:

$$c_{MQW} = 5.0834 \text{ \AA}; a_{MQW} = 3.1512 \text{ \AA}$$

It corresponds to composition of  $Al_xGa_{1-x}N$  with  $x=0.5$



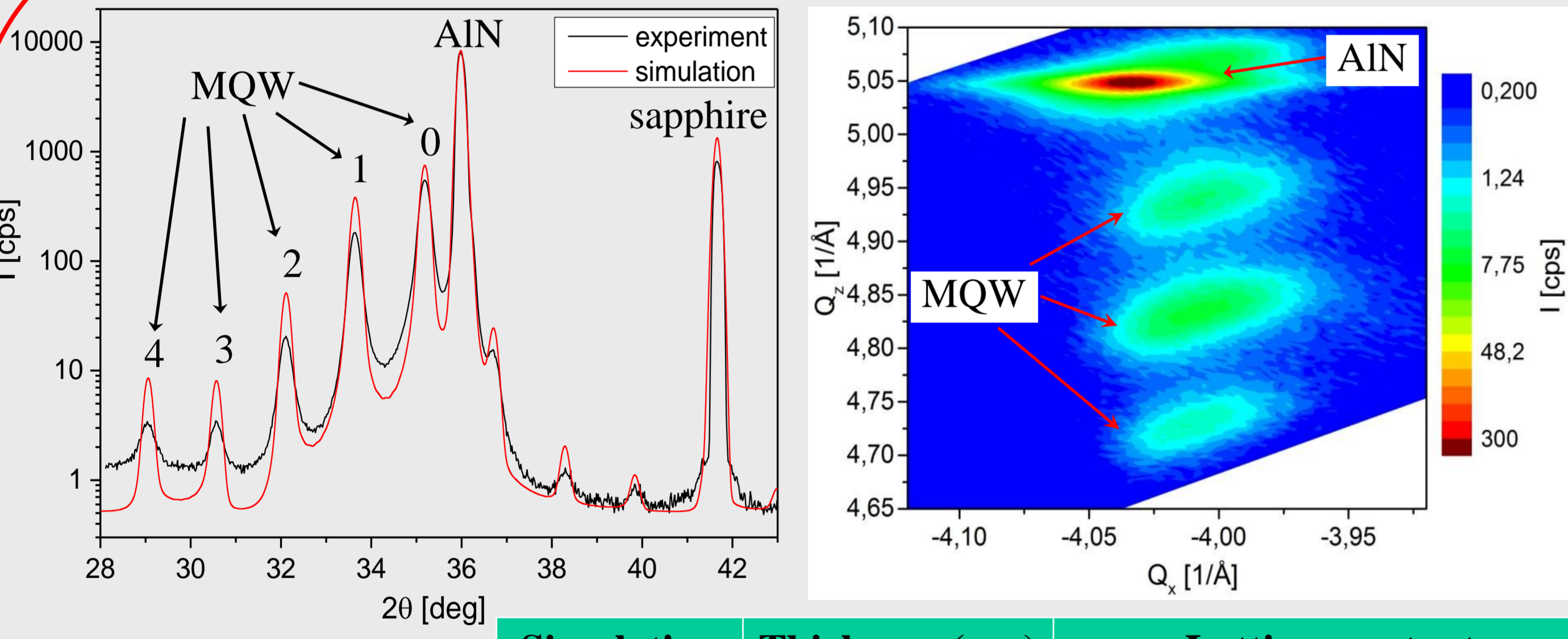
- Experimental 2 $\theta$ / $\omega$  scan of AlN/GaN 00.2 reflection shows 2nd order of peaks coming from MQWs
- Theoretical curve of 2 $\theta$ / $\omega$  scan of AlN/GaN 00.2 reflection is in a good agreement with experimental data
- The intensities varied because of the interface blurring and pinholes existing in the structure

Simulation	Thickness (nm)	Lattice constants
AIN	1.93	$c_{MQW} = 5.0957 \text{ \AA}$
GaN	1.95	$a_{MQW} = 3.1209 \text{ \AA}$
Total MQW	38.8	(it corresponds to composition of $Al_xGa_{1-x}N$ with $x=0.56$ )

- TEM images show good quality of interfaces in MQWs
- There are pinholes present in the structure

- RSM of 11.4 asymmetrical reflection shows partial relaxation of AlN/GaN MQWs
- Relaxation is equal to 30%

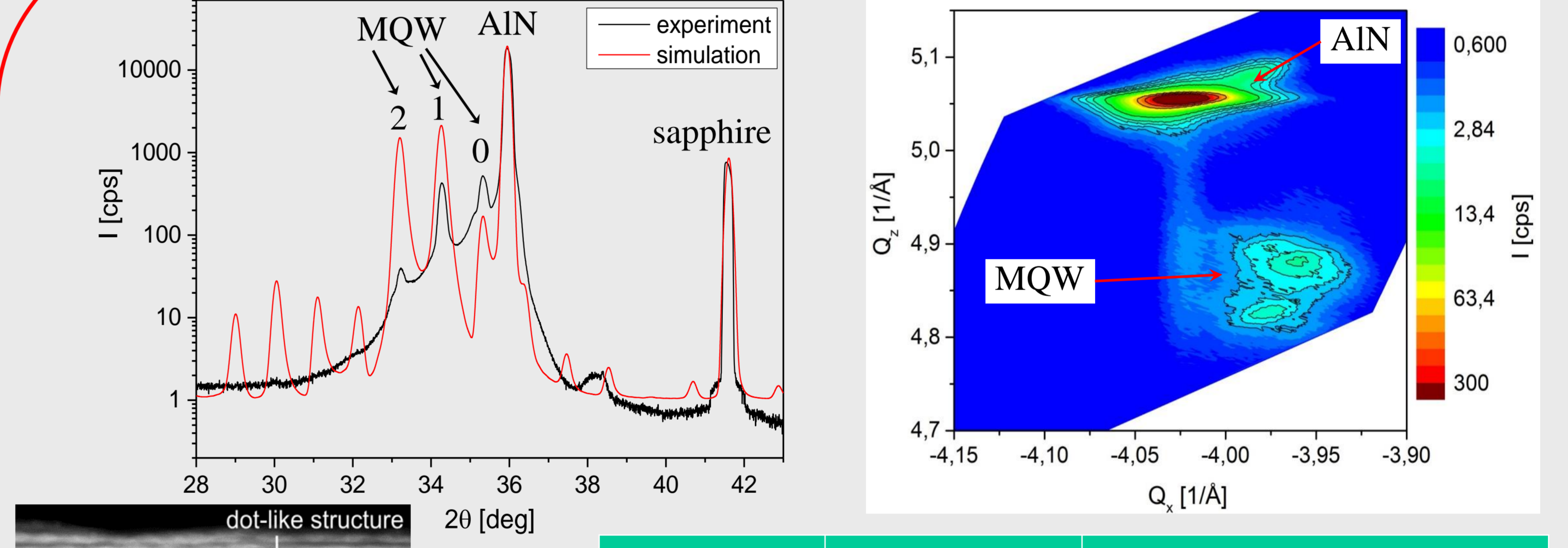
## Sample 2 – XRD, TEM



Simulation	Thickness (nm)	Lattice constants
AIN	3	$c_{MQW} = 5.0950 \text{ \AA}$
GaN	3	$a_{MQW} = 3.1275 \text{ \AA}$
Total MQW	60	(it corresponds to composition of $Al_xGa_{1-x}N$ with $x=0.54$ )

- Experimental 2 $\theta$ / $\omega$  scan of AlN/GaN 00.2 reflection shows 4th order of peaks coming from MQWs
- RSM of 11.4 asymmetrical reflection shows partial relaxation of AlN/GaN MQWs (relaxation = 27%)
- Very good quality of MQWs from TEM

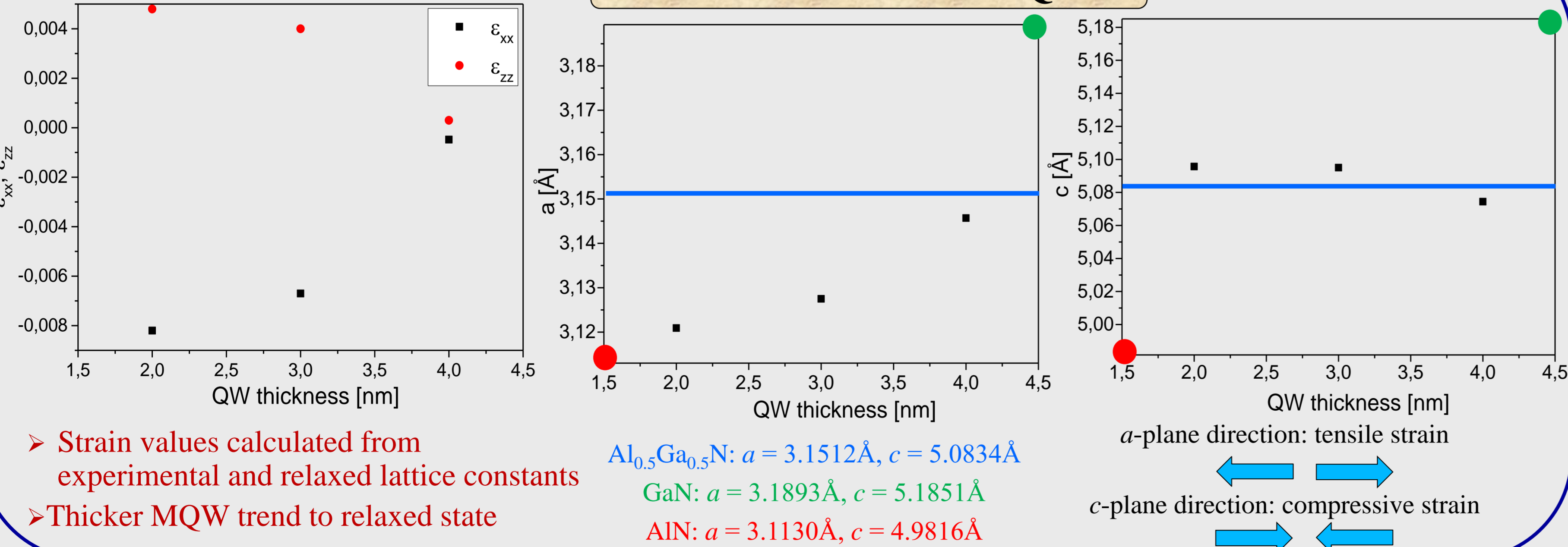
## Sample 3 – XRD, TEM



Simulation	Thickness (nm)	Lattice constants
AIN	2.3	$c_{MQW} = 5.0744 \text{ \AA}$
GaN	6.3	$a_{MQW} = 3.1457 \text{ \AA}$
Total MQW	86	(it corresponds to composition of $Al_xGa_{1-x}N$ with $x=0.55$ )

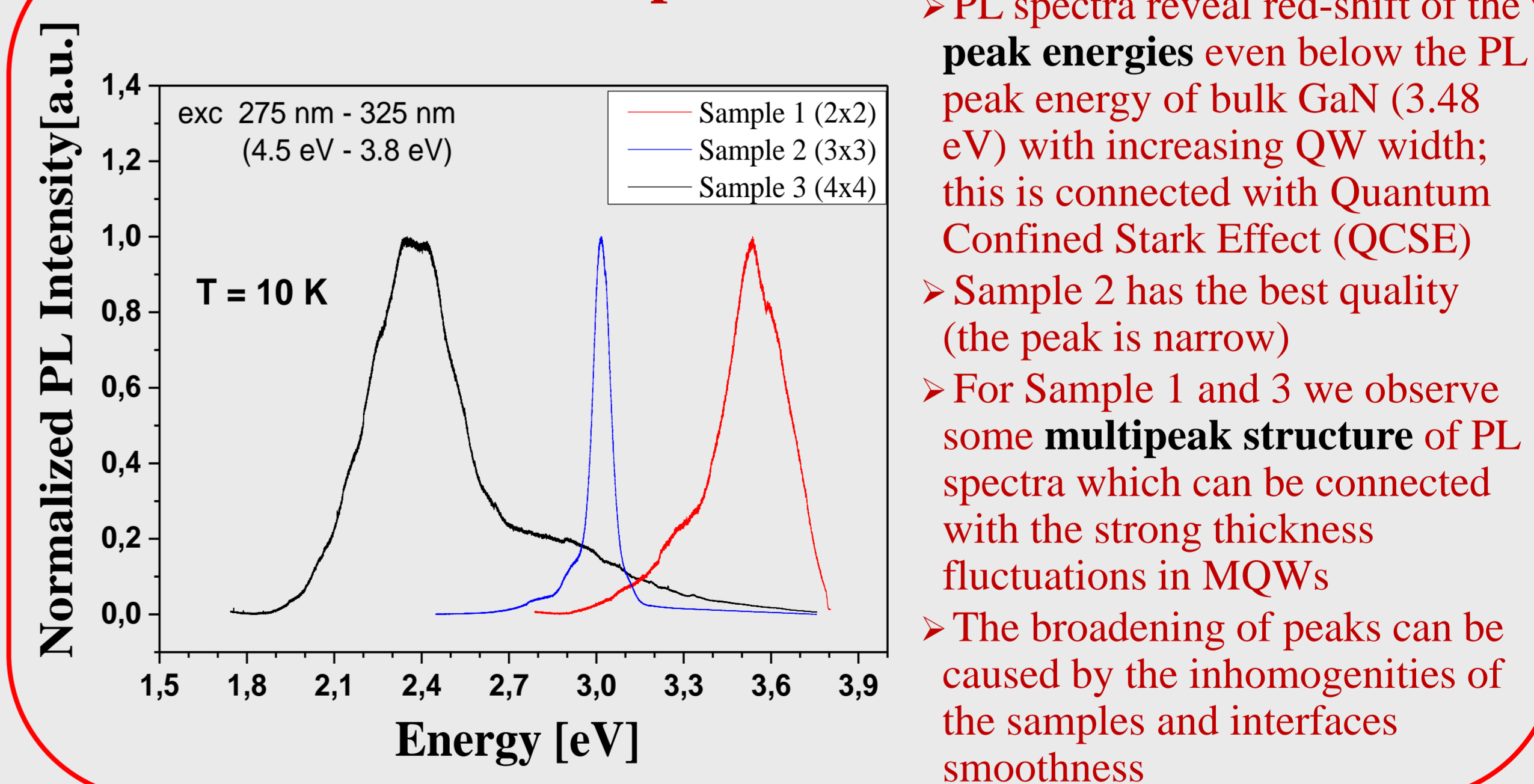
- Experimental 2 $\theta$ / $\omega$  scan of AlN/GaN 00.2 reflection shows only 2nd order of peaks coming from MQWs
- RSM of 11.4 asymmetrical reflection shows partial relaxation of AlN/GaN MQWs (relaxation = 30%)
- Bad quality of MQWs from TEM; pinholes, dot-like structure

## Strain relation in MQWs



- Strain values calculated from experimental and relaxed lattice constants
- Thicker MQW trend to relaxed state

## PL spectra



- PL spectra reveal red-shift of the peak energies even below the PL peak energy of bulk GaN (3.48 eV) with increasing QW width; this is connected with Quantum Confined Stark Effect (QCSE)
- Sample 2 has the best quality (the peak is narrow)
- For Sample 1 and 3 we observe some multipeak structure of PL spectra which can be connected with the strong thickness fluctuations in MQWs
- The broadening of peaks can be caused by the inhomogeneities of the samples and interfaces smoothness

## Conclusions

- For Sample 1 and 3 we observe existence of the pinholes or dot-like structure which lead to worse quality of XRD peaks; only few peaks coming from MQW are registered
- Sample 2 has the best quality, it has smooth interfaces; there are visible 4th order XRD peaks coming from MQWs
- MQWs with well and barrier thicknesses from 2 nm to 4 nm are in tensile strain in in-plane direction and in compressive strain in out-of-plane direction
- The thicker well/barrier is the more relaxed MQWs are
- Luminescence properties of the samples correlate well with XRD and TEM results: the better sample quality, the more efficient luminescence and narrow PL peak
- The PL spectra show red-shift with increasing of well/barrier thickness, which is connected with QCSE